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a common electrode having a function of a black matrix over said first interlayer insulating film;

a second interlayer insulating film over said common electrode;

B'ant- a pixel line and at least one pixel electrode both formed over the second interlayer insulating film, said pixel electrode extending from said pixel line; and

a liquid crystal layer over said pixel line and said pixel electrode;

wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;

wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and

wherein a storage capacitor is formed between said pixel line and said black matrix.

139. A device according to claim 138, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

140. A device according to claim 138, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative

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dielectric constant larger than that of said first interlayer insulating film.

B' ent. 141. A device according to claim 138, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

142. A device according to claim 138, wherein said thin film transistor has a semiconductor layer including a high-resistivity region.

143. A device according to claim 138, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

144. A device according to claim 138, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

145. A device according to claim 138, wherein said first interlayer insulating film serves as a planarization film.

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146. A liquid crystal display device comprising:

a first substrate;

a second substrate opposed to said first substrate;

a thin film transistor over said first substrate;

a first interlayer insulating over said thin film transistor;

a common electrode having a function of a black matrix over said first interlayer insulating;

a second interlayer insulating over said common electrode;

a pixel line and at least one pixel electrode both formed over said second interlayer insulating film; said pixel electrode extending from said pixel line over said second interlayer film; and

a liquid crystal layer over said pixel line and said pixel electrode;

wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;

wherein said liquid crystal layer is driven by an electric field formed between the pixel electrode and the common electrode, the electric field having a component parallel with said first substrate; and

wherein a storage capacitor is formed between said pixel line and said black matrix.

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147. A device according to claim 146, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

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148. A device according to claim 146, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating.

149. A device according to claim 146, wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

150. A device according to claim 146, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

151. A device according to claim 146, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

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152. A device according to claim 146, wherein said first interlayer insulating film serves as a planarization film.

153. A liquid crystal display device comprising:

a substrate;

a thin film transistor over said substrate;

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a first interlayer insulating film comprising an organic resin over said thin film transistor;

a common electrode having a function of a black matrix over said first interlayer insulating film;

a second interlayer insulating film over said common electrode;

a pixel line and at least one pixel electrode both formed over said second interlayer insulating film, said pixel electrode extending from said pixel line; and

a liquid crystal layer over said pixel line and said pixel electrode;

wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;

wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and

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wherein a storage capacitor is formed between said pixel line and said black matrix.

154. A device according to claim 153, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

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155. A device according to claim 153, wherein said second interlayer insulating film comprises at least an organic resin material and an inorganic material and has a relative dielectric constant larger than that of said first interlayer insulating film.

156. A device according to claim 153 wherein said second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

157. A device according to claim 153, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

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158. A device according to claim 153, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

159. A device according to claim 153, wherein said first interlayer insulating film serves as a planarization film.

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160. A liquid crystal display device comprising:
a substrate;
a thin film transistor over said substrate;
a first interlayer insulating film over said thin film transistor;

a common electrode having a function of a black matrix over said first interlayer insulating film;

a second interlayer insulating film over said common electrode, said second interlayer insulating film comprising at least a first layer comprising an organic resin material and a second layer comprising an inorganic material;

a pixel line and at least one pixel electrode both formed over said second interlayer insulating film, said pixel electrode extending from said pixel line; and

a liquid crystal layer over said pixel line and said pixel electrode;

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wherein said pixel electrode is electrically connected to the thin film transistor through said pixel line;

wherein said liquid crystal layer is driven by an electric field formed between said pixel electrode and said common electrode, said electric field having a component parallel with said substrate; and

wherein a storage capacitor is formed between said pixel line and said black matrix.

161. A device according to claim 160, wherein said pixel electrode has a width in a range of 0.1 to 2.0 μm .

162. A device according to claim 160, wherein said second layer of the second interlayer insulating film comprises one or a plurality of materials selected from the group consisting of AlN , AlN_xO_y , Si_3N_4 , and SiO_xN_y .

163. A device according to claim 160, wherein said first interlayer insulating film has a thickness in a range of 0.1 to 5.0 μm , and wherein said second interlayer insulating film has a thickness in a range of 0.01 to 1.0 μm .

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164. A device according to claim 160, wherein said thin film transistor has a semiconductor layer that is separated into a base region and a floating island region.

165. A device according to claim 160, wherein said first interlayer insulating film serves as a planarization film.
